Amendment to the Claims:

This listing of claims replaces all prior versions, and listings, of claims in the application:

1. (Currently Amended) An apparatus comprising:

first and second Controlled Collapse Chip Connection bumps;

a unitary first metal layer coupled to the first and second bumps, the first metal layer being formed in a trench of a dielectric layer, the first metal layer being coupled to a top metal layer of an integrated circuit die, the first metal layer being adapted to transfer current from the first and second bumps to the top metal layer of the integrated circuit die; and

a unitary second metal layer over the first metal layer, the second metal layer being coupled to the first bump, a third bump and the first metal layer, the second metal layer being adapted to transfer current from the first and third bumps to the first metal layer.

2. (Currently Amended) The apparatus of Claim 1, wherein the third ~~first and second~~ bump~~s are~~ is a Controlled Collapse Chip Connection bump~~s~~.

3. (Original) The apparatus of Claim 1, wherein the first and second bumps are coupled to first and second solder bumps of a substrate.

4. (Original) The apparatus of Claim 1, wherein the first metal layer is about 10 to 50 microns thick.

5. (Original) The apparatus of Claim 1, wherein the first metal layer comprises electroplated copper.

6. (Currently Amended) The apparatus of Claim 1, wherein the first metal layer is deposited in vias over a ~~unitary~~ first base layer metallization, which is deposited over the top metal layer of the integrated circuit die.

7. (Original) The apparatus of Claim 1, further comprising a first dielectric layer enclosing the first metal layer.

8. (Original) The apparatus of Claim 7, wherein the first dielectric layer comprises a self-planarizing, photo-definable polymer.

9. (Original) The apparatus of Claim 7, wherein the first dielectric layer comprises a self-planarizing, non-photo-definable polymer.

10. (Canceled).

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10 ~~11.~~ (Currently Amended) The apparatus of Claim 1 ~~10~~, wherein the second metal layer is orthogonal to the first metal layer.

11 ~~12.~~ (Previously Presented) The apparatus of Claim 1, further comprising a unitary diffusion barrier over and on sides of the first metal layer.

13-28. (Canceled).

12 ~~29.~~ (Currently Amended) The apparatus of Celaim 3, wherein current from the substrate is spread to both of the first and second solder bumps and then to both of the first and second Controlled Collapse Chip Connection bumps.

13 ~~30.~~ (New) An apparatus comprising:

first and second connection means;

a unitary first metal layer coupled to the first and second connection means, the first metal layer being formed in a trench of a dielectric layer, the first metal layer being coupled to a top metal layer of an integrated circuit die, the first metal layer being adapted to transfer current from the first and

second connection means to the top metal layer of the integrated circuit die; and

a unitary second metal layer over the first metal layer, the second metal layer being coupled to the first connection means, a third connection means and the first metal layer, the second metal layer being adapted to transfer current from the first and third connection means to the first metal layer.

14 ~~31.~~ (New) The apparatus of Claim 13 ~~30~~, wherein the first, second, and third connection means are Controlled Collapse Chip Connection bumps.

15 ~~32.~~ (New) The apparatus of Claim 13 ~~30~~, wherein the first and second connection means are coupled to first and second solder bumps of a substrate.

16 ~~33.~~ (New) The apparatus of Claim 13 ~~30~~, wherein the first metal layer is deposited in vias over a first base layer metallization, which is deposited over the top metal layer of the integrated circuit die.

17 ~~34.~~ (New) The apparatus of Claim 13 ~~30~~, further comprising dielectric layering means enclosing the first metal layer.

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18 ~~35~~. (New) The apparatus of Claim 17 ~~34~~, wherein the first dielectric layer means comprises self-planarizing, photo-definable polymer.

19 ~~36~~. (New) The apparatus of Claim 17 ~~34~~, wherein the first dielectric layer means comprises self-planarizing, non-photo-definable polymer.

20 ~~37~~. (New) The apparatus of Claim 17 ~~34~~, wherein the second metal layer is orthogonal to the first metal layer.

24 ~~38~~. (New) An apparatus comprising:

first and second connection means;

Amdt. first layer means coupled to the first and second connection means, the first layer means being formed in a trench of a dielectric layer, the first layer means being coupled to a top metal layer of an integrated circuit die, the first layer means being adapted to transfer current from the first and second connection means to the top metal layer of the integrated circuit die; and

Amdt. second layer means over and orthogonal to the first layer means, the second layer means layer being coupled to the first connection means, a third connection means and the first layer means, the second layer means being adapted to transfer current

from the first and third connection means to the first layer means.

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~~39.~~ (New) The apparatus of Claim ~~38~~, wherein the first, second, and third connection means are Controlled Collapse Chip Connection bumps.

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~~40.~~ (New) The apparatus of Claim ~~38~~, wherein the first and second connection means are coupled to first and second solder bumps of a substrate.

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~~41.~~ (New) The apparatus of Claim ~~38~~, wherein the first layer means is deposited in vias over a first base layer metallization, which is deposited over the top metal layer of the integrated circuit die.

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~~42.~~ (New) The apparatus of Claim ~~38~~, further comprising dielectric layering means enclosing the first metal layer.

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~~43.~~ (New) The apparatus of Claim ~~34~~, wherein the first dielectric layer means comprises self-planarizing, photo-definable polymer.

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~~44.~~ 22 (New) The apparatus of Claim ~~34~~ 17, wherein the first dielectric layer means comprises self-planarizing, non-photo-definable polymer.

~~45.~~ 23 (New) The apparatus of Claim ~~34~~ 17, further comprising diffusion barrier means over and on sides of the first layer means.